

Schottky barrier diode

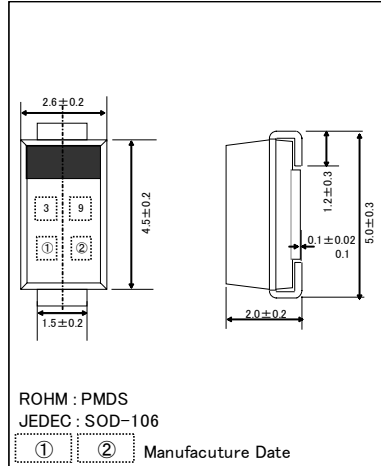
RB081L-20

● **Applications**
General rectification

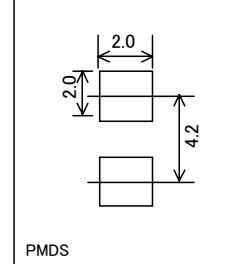
● **Features**
1) Small power mold type. (PMDS)
2) Low V_F , Low I_R .
3) High reliability.

● **Construction**
Silicon epitaxial planar

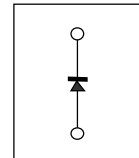
● **External dimensions (Unit : mm)**



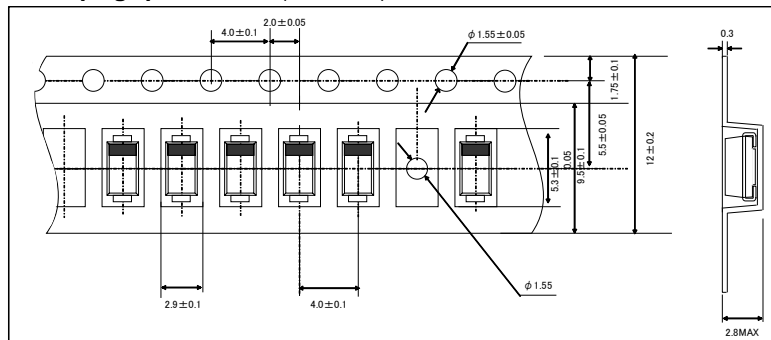
● **Land size figure (Unit : mm)**



● **Structure**



● **Taping specifications (Unit : mm)**



● **Absolute maximum ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	25	V
Reverse voltage (DC)	V_R	20	V
Average rectified forward current (*1)	I_o	5	A
Forward current surge peak (60Hz·1cyc)	I_{FSM}	70	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

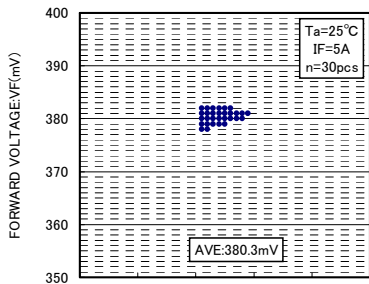
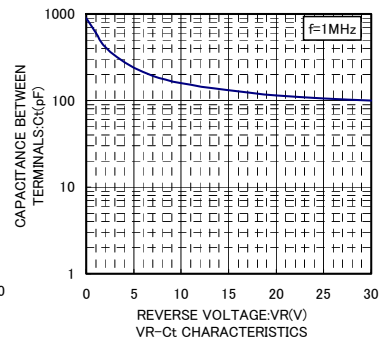
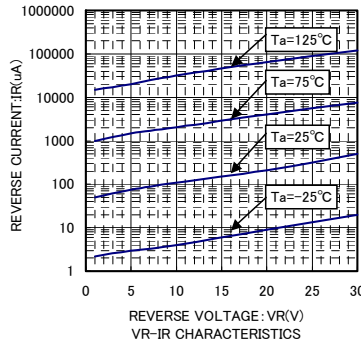
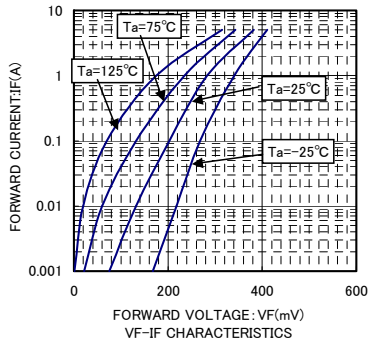
(*1) Mounted on epoxy board. 180° Harf sine wave

● **Electrical characteristics (Ta=25°C)**

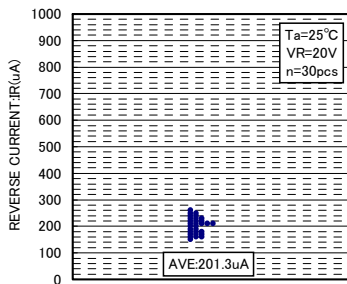
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.45	V	$I_F=0.5A$
Reverse current	I_R	-	-	700	μA	$V_R=20V$

Diodes

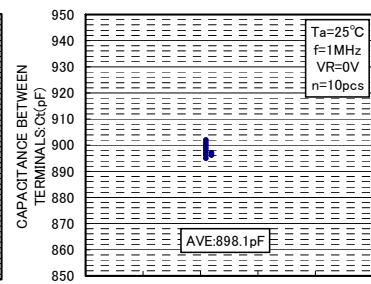
●Electrical characteristic curves (Ta=25°C)



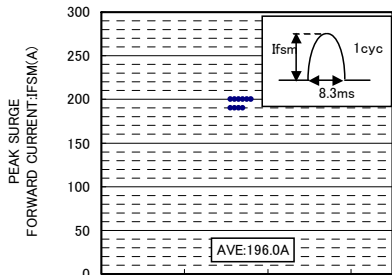
VF DISPERSION MAP



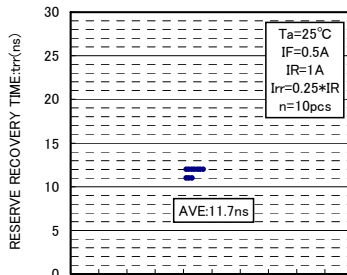
IR DISPERSION MAP



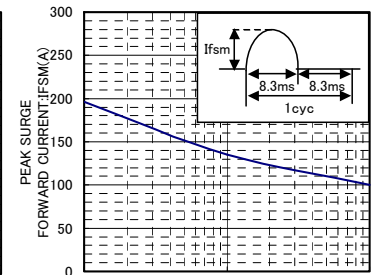
Ct DISPERSION MAP



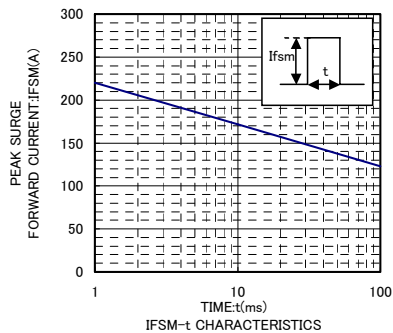
IFSM DISERSION MAP



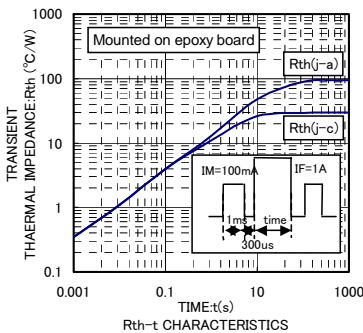
trr DISPERSION MAP



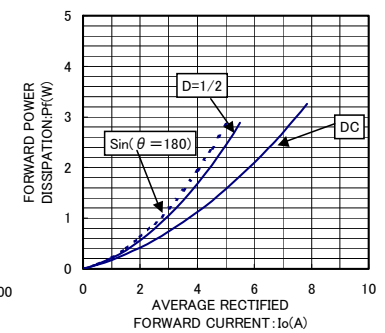
IFSM-CYCLE CHARACTERISTICS



IFSM-t CHARACTERISTICS

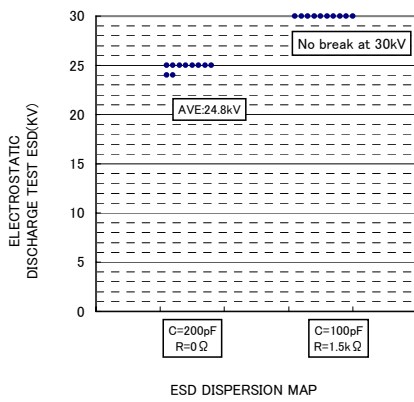
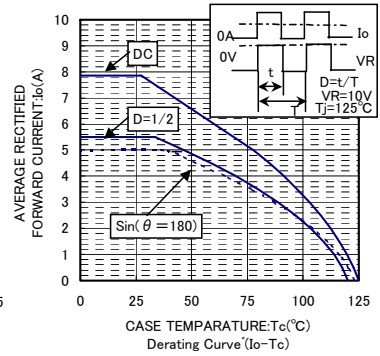
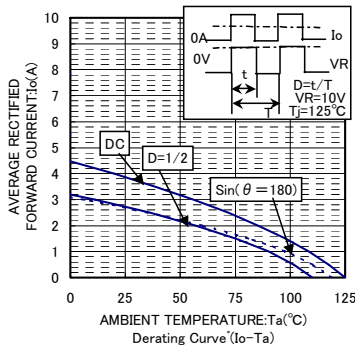
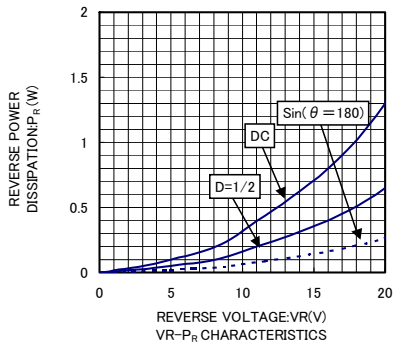


Rth-t CHARACTERISTICS



Io-Pf CHARACTERISTICS

Diodes



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